



Sample &

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CSD18501Q5A

SLPS319C - JUNE 2012 - REVISED JANUARY 2015

CSD18501Q5A 40 V N-Channel NexFET™ Power MOSFET

Features 1

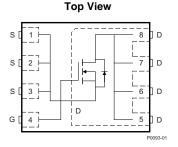
- Ultra low Q_a and Q_{ad}
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- **RoHS** Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

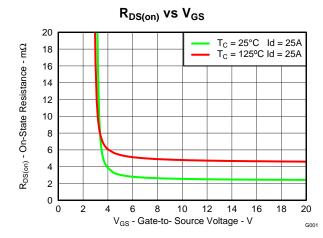
Applications 2

- **DC-DC** Conversion
- Secondary Side Synchronous Rectifier
- **Battery Motor Control**

3 Description

This 40 V, 2.5 mΩ, SON 5 × 6 mm NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications.





Product Summary

T _A = 25	°C	TYPICAL VA	UNIT		
V _{DS}	Drain-to-Source Voltage 40				
Qg	Gate Charge Total (4.5 V)	20	nC		
Q _{gd}	Gate Charge Gate-to-Drain	5.9	nC		
P	Drain-to-Source On-Resistance	V _{GS} = 4.5 V 3.3		mΩ	
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V 2.5		mΩ	
V _{GS(th)}	Threshold Voltage	1.8	V		

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship					
CSD18501Q5A 2500		13-Inch Reel	SON 5 mm × 6 mm	Tape and					
CSD18501Q5AT	250	7-Inch Reel	Plastic Package	Reel					

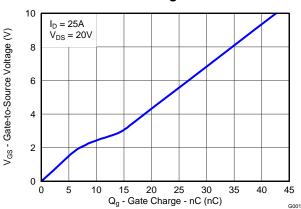
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 2$	25°C	VALUE	UNIT	
V_{DS}	Drain-to-Source Voltage	40	V	
V_{GS}	Gate-to-Source Voltage	±20	V	
	Continuous Drain Current (Package limited)	100		
I _D	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	161	A	
	Continuous Drain Current (1)	22	А	
I _{DM}	Pulsed Drain Current (2)	400	А	
-	Power Dissipation ⁽¹⁾	3.1	14/	
PD	Power Dissipation, $T_C = 25^{\circ}C$	150	W	
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C	
E _{AS}	Avalanche Energy, Single Pulse I_D = 68 A, L = 0.1 mH, R_G = 25 Ω	231	mJ	

(1) Typical $R_{\theta JA} = 40^{\circ}$ C/W on a 1-inch², 2-oz. Cu pad on a 0.06inch thick FR4 PCB.

(2) Max $R_{\theta JC} = 1.0^{\circ}C/W$, Pulse duration $\leq 100\mu s$, duty cycle $\leq 1\%$



Gate Charge

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (October 2012) to Revision C

•	Added part number to title	. 1
•	Added 7-inch reel to Ordering Information table	. 1
•	Increased silicon limited continuous drain current to 161 A	. 1
•	Increased pulsed drain current to 400 A	. 1
•	Added line for max power dissipation with case temperature held to 25° C	. 1
•	Updated pulsed current conditions	. 1
•	Updated Figure 1 to a normalized R _{eJC} curve	. 4
	Updated the SOA in Figure 9	
•	Added Recommended Stencil Opening	. 9

Changes from Revision A (June 2012) to Revision B

•	Changed the Transconductance TYP value From: 142 S To: 118 S	. 3
•	Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: I_{DS} = 25 A, R_G = 2 Ω To: I_{DS} = 25 A, R_G = 0 Ω	. 3
•	Changed the Q _{rr} Reverse Recovery Charge TYP value From: 21 nC To: 70 nC	

Changes from Original (June 2012) to Revision A					
•	Added "T₄ = 25°C" to the Product Summary table	1	-		

Q5A Tape and Reel Information 10

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS		I		
BV _{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	40		V
I _{DSS}	Drain-to-Source Leakage Current	$V_{GS} = 0 V, V_{DS} = 32 V$		1	μA
I _{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0 V, V_{GS} = 20 V$		100	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.4 1.8	2.3	V
	Drain to Course On Desistence	V _{GS} = 4.5 V, I _D = 25 A	3.3	4.3	mΩ
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 10 V, I _D = 25 A	2.5	3.2	mΩ
9 _{fs}	Transconductance	V _{DS} = 20 V, I _D = 25 A	118		S
DYNAMI	C CHARACTERISTICS				
C _{iss}	Input Capacitance		3200	3840	pF
C _{oss}	Output Capacitance	$V_{GS} = 0 V, V_{DS} = 20 V,$ f = 1 MHz	725	870	pF
C _{rss}	Reverse Transfer Capacitance		18	23	pF
R_G	Series Gate Resistance		1.2	2.4	Ω
Qg	Gate Charge Total (4.5 V)		20	24	nC
Qg	Gate Charge Total (10 V)		42	50	
Q _{gd}	Gate Charge Gate-to-Drain	V _{DS} = 20 V, I _D = 25 A	5.9		nC
Q _{gs}	Gate Charge Gate-to-Source		8.1		nC
Q _{g(th)}	Gate Charge at Vth		5.7		nC
Q _{oss}	Output Charge	V _{DS} = 20 V, V _{GS} = 0 V	48		nC
t _{d(on)}	Turn On Delay Time		4.7		ns
t _r	Rise Time	$V_{DS} = 20 V, V_{GS} = 10 V,$	10		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 25 \text{ A}, \text{ R}_{G} = 0$	20		ns
t _f	Fall Time		3.4		ns
DIODE C	HARACTERISTICS		·		
V_{SD}	Diode Forward Voltage	I _{DS} = 25 A, V _{GS} = 0 V	0.8	1	V
Q _{rr}	Reverse Recovery Charge		70		nC
t _{rr}	Reverse Recovery Time	V_{DS} = 20 V, I _F = 25 A, di/dt = 300 A/µs	40		ns

5.2 Thermal Information

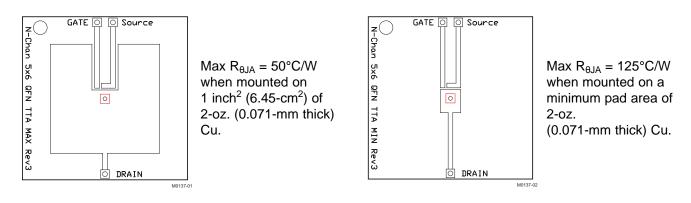
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance ⁽¹⁾			1.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ⁽¹⁾⁽²⁾			50	°C/W

R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inches x 1.5-inches (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

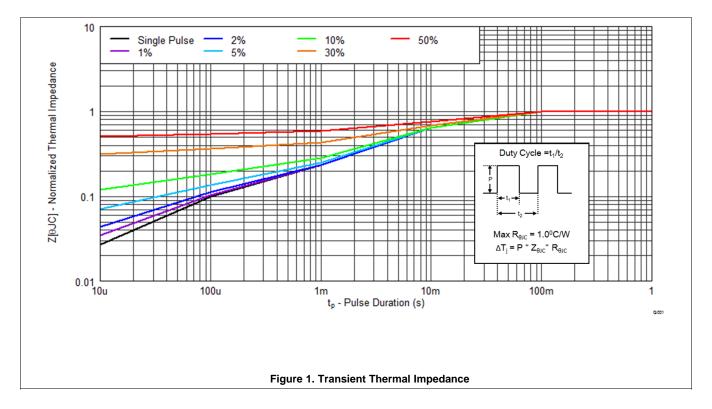
(2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





5.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

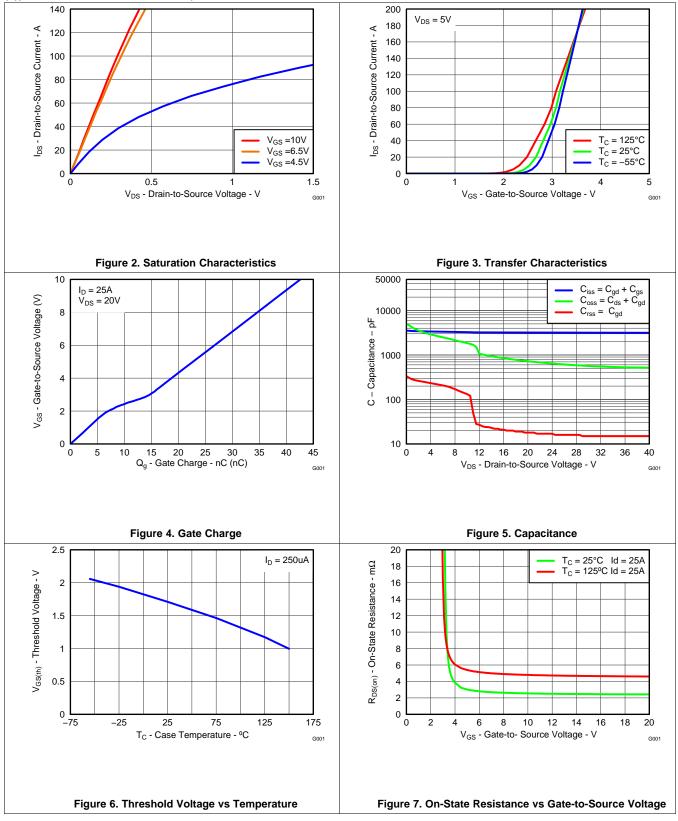


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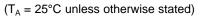
Typical MOSFET Characteristics (continued)

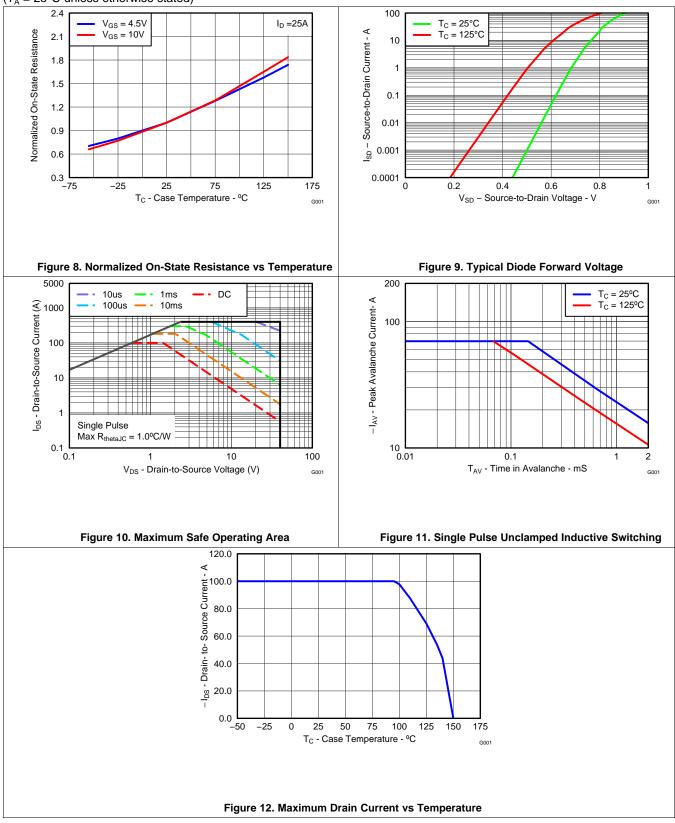
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





Typical MOSFET Characteristics (continued)







6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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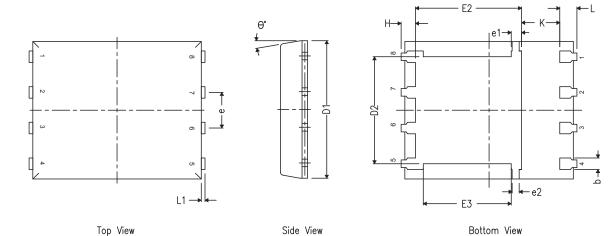
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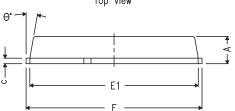
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions



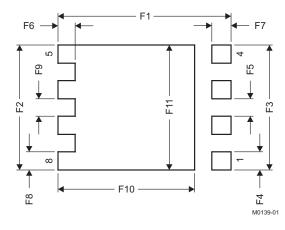




DIM		MILLIMETERS	
DIM	MIN	NOM	MAX
А	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
E3	3.03	3.13	3.23
е	1.17	1.27	1.37
e1	0.27	0.37	0.47
e2	0.15	0.25	0.35
н	0.41	0.56	0.71
К	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°	_	12°



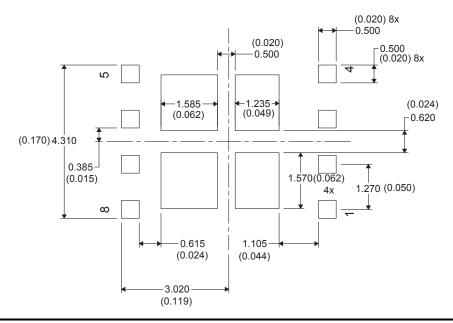
7.2 Recommended PCB Pattern



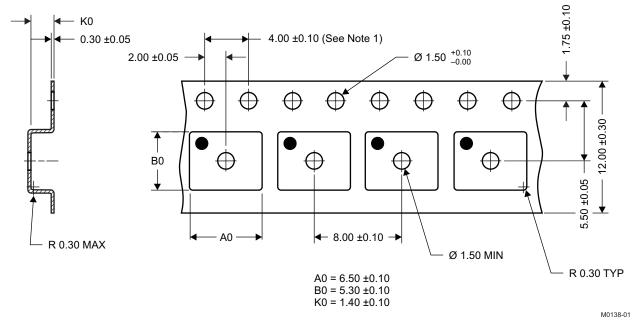
DIM	MILLIM	ETERS	INCHES			
DIN	MIN	МАХ	MIN	MAX		
F1	6.205	6.305	0.244	0.248		
F2	4.46	4.56	0.176	0.18		
F3	4.46	4.56	0.176	0.18		
F4	0.65	0.7	0.026	0.028		
F5	0.62	0.67	0.024	0.026		
F6	0.63	0.68	0.025	0.027		
F7	0.7	0.8	0.028	0.031		
F8	0.65	0.7	0.026	0.028		
F9	0.62	0.67	0.024	0.026		
F10	4.9	5	0.193	0.197		
F11	4.46	4.56	0.176	0.18		

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

7.3 Recommended Stencil Opening



7.4 Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD18501Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18501	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

7-Jan-2015

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



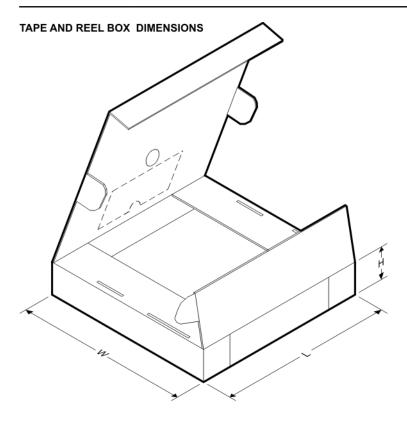
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18501Q5A	VSONP	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18501Q5A	VSONP	DQJ	8	2500	340.0	340.0	38.0

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